## **HIGH-SIDE CURRENT MONITOR**

#### **DESCRIPTION**

The ZXCT1009 is a high side current sense monitor. Using this device eliminates the need to disrupt the ground plane when sensing a load current.

It takes a high side voltage developed across a current shunt resistor and translates it into a proportional output current.

A user defined output resistor scales the output current into a ground-referenced voltage.

The wide input voltage range of 20V down to as low as 2.5V make it suitable for a range of applications. A minimum operating current of just  $4\mu A$ , combined with its SOT23 package make it a unique solution for portable battery equipment.

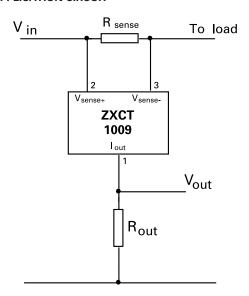
#### **FEATURES**

- Low cost, accurate high-side current sensing
- · Output voltage scaling
- Up to 2.5V sense voltage
- 2.5V 20V supply range
- 4µA quiescent current
- 1% typical accuracy
- SOT23 and SM8 packages

#### **APPLICATIONS**

- Battery chargers
- Smart battery packs
- DC motor control
- · Over current monitor
- Power management
- · Level translating
- Programmable current source

#### APPLICATION CIRCUIT



## **ORDERING INFORMATION**

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	PARTMARKING	PACKAGE
ZXCT1009FTA	7″	8mm	3,000 units	109	SOT23
ZXCT1009T8TA	7"	12mm	1,000 units	ZXCT1009	SM8



## **ABSOLUTE MAXIMUM RATINGS**

Voltage on any pin -0.6V to 20V (relative to Iout)

Continuous output current

Continuous sense voltage  $V_{in} + 0.5V > V_{sense}^{\dagger} > V_{in} - 5V$ 

Operating temperature -40 to 85°C -55 to 125°C Storage temperature Package power dissipation  $(T_A = 25^{\circ}C)$ 

SOT23 450mW - derate to zero at 125°C

SM8 2W

Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings for extended periods may reduce device reliability.

## **ELECTRICAL CHARACTERISTICS**

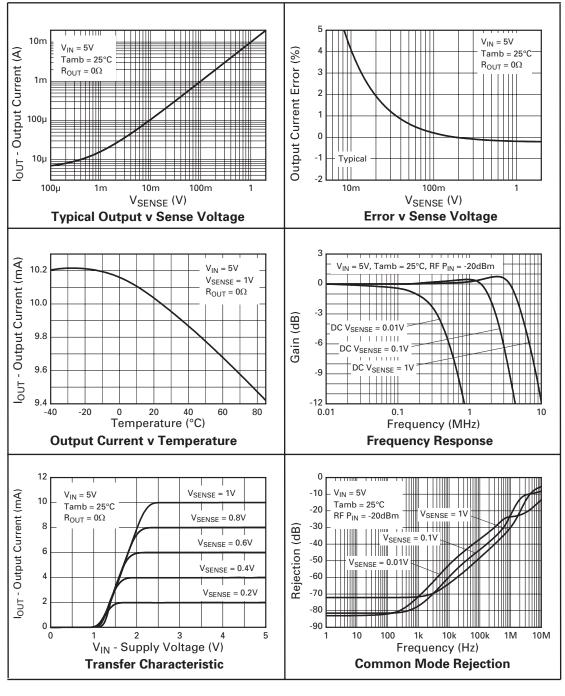
Test Conditions TA =  $25^{\circ}$ C,  $V_{in}$  = 5V,  $R_{out}$  =  $100\Omega$ .

SYMBOL	PARAMETER	CONDITIONS	LIMITS		UNIT	
			Min	Тур	Max	
Vin	V <sub>CC</sub> range		2.5		20	V
l <sub>out</sub> <sup>1</sup>	Output current	V <sub>sense</sub> =0V	1	4	15	μΑ
		V <sub>sense</sub> =10mV	90	104	120	μΑ
		V <sub>sense</sub> =100mV	0.975	1.002	1.025	mA
		V <sub>sense</sub> =200mV	1.95	2.0	2.05	mA
		V <sub>sense</sub> =1V	9.6	9.98	10.2	mA
V <sub>sense</sub> †	Sense voltage		0		2500	mV
I <sub>sense</sub> -	V <sub>sense</sub> -				100	nA
	input current					
Acc	Accuracy	$R_{sense} = 0.1\Omega$				
		V <sub>sense</sub> =200mV	-2.5		2.5	%
Gm	Transconductance,			10000		μ <b>A</b> /V
	I <sub>out</sub> / V <sub>sense</sub>					
BW	Bandwidth	RF P <sub>in</sub> = -20dBm‡ V <sub>sense</sub> = 10mV dc		300		kHz
		$V_{\text{sense}} = 100 \text{mV dc}$		2		MHz

 $<sup>^1</sup>$  Includes input offset voltage contribution  $^\dagger Vsense=Vin\text{-}Vload \\ \ddagger \text{-}20dBm=63mVp\text{-}p into 50\Omega$ 

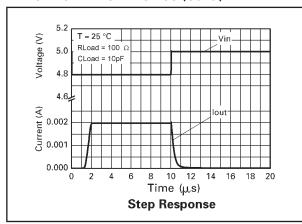


## **TYPICAL CHARACTERISTICS**

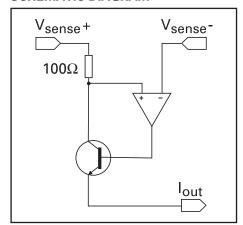




# **TYPICAL CHARACTERISTICS (Cont.)**



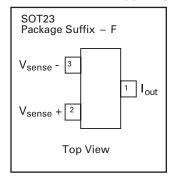
## **SCHEMATIC DIAGRAM**

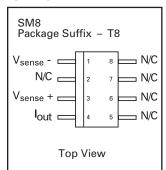


## **PIN DESCRIPTION**

Pin Name	Pin Function			
V <sub>sense+</sub>	Supply voltage			
V <sub>sense</sub> -	Connection to load/battery			
l <sub>out</sub>	Output current, proportional to V <sub>in</sub> -V <sub>load</sub>			

## **CONNECTION DIAGRAMS**







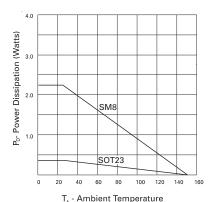
#### **POWER DISSIPATION**

The maximum allowable power dissipation of the device for normal operation (Pmax), is a function of the package junction to ambient thermal resistance (θja), maximum junction temperature (Tjmax), and ambient temperature (Tamb), according to the expression:

 $P_{max} = (T_{jmax} - T_{amb}) / \theta_{ja}$ 

The device power dissipation, PD is given by the expression:

PD=Iout.(Vin-Vout) Watts



#### **APPLICATIONS INFORMATION**

The following lines describe how to scale a load current to an output voltage.

E.g.

A 1A current is to be represented by a 100mV output voltage:

1)Choose the value of  $R_{sense}$  to give  $50mV > V_{sense} > 500mV$  at full load.

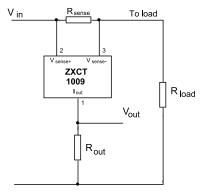
For example  $V_{sense} = 100 mV$  at 1.0A.  $R_{sense} = 0.1/1.0 \Rightarrow 0.1$  ohms.

2)Choose  $R_{out}$  to give  $V_{out}$  = 100mV, when  $V_{sense}$  = 100mV.

Rearranging  $^{1}$  for Rout gives: Rout = Vout /(Vsense x 0.01)

 $R_{out} = 0.1 / (0.1 \times 0.01) = 100 \Omega$ 

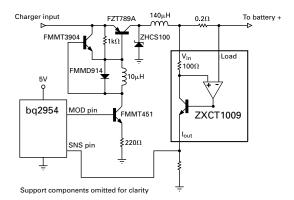
#### TYPICAL CIRCUIT APPLICATION



Where R<sub>load</sub> represents any load including DC motors, a charging battery or further circuitry that requires monitoring, R<sub>sense</sub> can be selected on specific requirements of accuracy, size and power rating.



#### **APPLICATIONS INFORMATION (Continued)**



# Li-Ion Charger Circuit

The above figure shows the ZXCT1009 supporting the Benchmarq bq2954 Charge Management IC. Most of the support components for the bq2954 are omitted for clarity. This design also uses the Zetex FZT789A high current Super- $\beta$  PNP as the switching transistor in the DC-DC step down converter and the FMMT451 as the drive NPN for the FZT789A. The circuit can be configured to charge up to four Li-lon cells at a charge current of 1.25A. Charge can be terminated on maximum voltage, selectable minimum current, or maximum time out. Switching frequency of the PWM loop is approximately 120kHz.

The ZXCT1009 is intended as a direct functional replacement for the ZDS1009, which is featured in a complete design from Unitrode/Texas Instruments on the Li-lon charger circuit shown above. Reference: DVS2954S1H Li-lon Charger Development System.

#### **Transient Protection**

An additional resistor, Rlim can be added in series with Rout (figure 1.0), to limit the current from lout. Any circuit connected to Vout will be protected from input voltage transients. This can be of particular use in automotive applications where load dump and other common transients need to be considered.

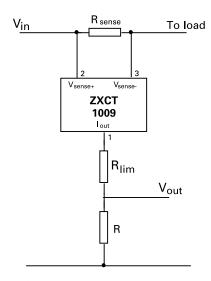


Figure 1.0 ZXCT1009 with additional current limiting Resistor Rlim.

Assuming the worst case condition of  $V_{out}$  = 0V; providing a low impedance to a transient, the minimum value of  $R_{lim}$  is given by:-

$$R_{lim}(min) = \frac{V_{pk} - V_{max}}{I_{pk}}$$

 $V_{pk} = \text{Peak transient voltage to be withstood} \ V_{max} = \text{Maximum working Voltage} = 20V \ I_{pk} = \text{Peak output current} = 40\text{mA}$ 

The maximum value of R<sub>lim</sub> is set by V<sub>in</sub>(min), V<sub>out</sub>(max) and the dropout voltage (see transfer characteristic on page 3) of the ZXCT1009:-

$$R_{lim}(max) = \frac{R_{out}[V_{in}(min) - (V_{dp} + V_{out}(max))]}{V_{out}(max)}$$

 $\begin{array}{l} \text{Vin(min)} = \text{Minimum Supply Operating Voltage} \\ \text{V}_{dp} = \text{Dropout Voltage} \\ \text{V}_{out} \ \ (\text{max}) = \ \ \text{Maximum Operating Output Voltage} \\ \end{array}$ 

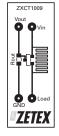


# **APPLICATIONS INFORMATION (Continued)**

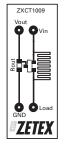
# PCB trace shunt resistor for low cost solution

The figure below shows output characteristics of the device when using a PCB resistive trace for a low cost solution in replacement for a conventional shunt resistor. The graph shows the linear rise in voltage across the resistor due to the PTC of the material and demonstrates how this rise in resistance value over temperature compensates for the NTC of the device.

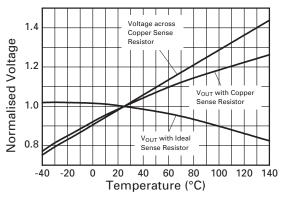
The figure opposite shows a PCB layout suggestion. The resistor section is 25mm x 0.25mm giving approximately  $150m\Omega$  using 1oz copper. The data for the normalised graph was obtained using a 1A load current and a  $100\Omega$  output resistor. An electronic version of the PCB layout is available at www.zetex.com/isense.



Actual Size



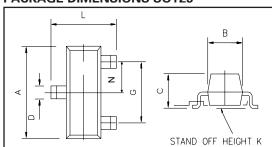
Layout shows area of shunt resistor compared to SOT23 package. Not actual size



Effect of Sense Resistor Material on Temperature Performance

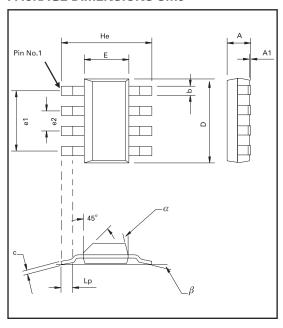


# **PACKAGE DIMENSIONS SOT23**



DIM	Millin	neters	Inches		
	Min	Max	Min	Max	
Α	2.67	3.05	0.105	0.120	
В	1.20	1.40	0.047	0.055	
С	-	1.10	-	0.043	
D	0.37	0.53	0.0145	0.021	
F	0.085	0.15	0.0033	0.0059	
G	NOM	1 1.9	NOM 0.075		
K	0.01	0.10	0.0004	0.004	
L	2.10	2.50	0.0825	0.0985	
N	NOM	0.95	NOM 0.037		

# **PACKAGE DIMENSIONS SM8**



DIM	Millimeters			Inches		
	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.7	-	_	0.067
A1	0.02	-	0.1	0.0008	_	0.004
b	-	0.7	-	-	0.028	-
С	0.24	-	0.32	0.009	_	0.013
D	6.3	-	6.7	0.248	_	0.264
Е	3.3	-	3.7	0.130	_	0.145
e1	-	4.59	-	-	0.180	_
e2	_	1.53	-	_	0.060	_
He	6.7	_	7.3	0.264	_	0.287
Lp	0.9	-	-	0.035	-	-
α	-	-	15°	-	_	15°
β	-	10°	-	-	10°	-

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Europe	Americas	Asia Pacific	Corporate Headquarters	
Zetex GmbH	Zetex Inc	Zetex (Asia) Ltd	Zetex Semiconductors plc	
Streitfeldstraße 19	700 Veterans Memorial Hwy	3701-04 Metroplaza Tower 1	Zetex Technology Park	
D-81673 München	Hauppauge, NY 11788	Hing Fong Road, Kwai Fong	Chadderton, Oldham, OL9 9LL	
Germany	USA	Hong Kong	United Kingdom	
Telefon: (49) 89 45 49 49 0	Telephone: (1) 631 360 2222	Telephone: (852) 26100 611	Telephone (44) 161 622 4444	
Fax: (49) 89 45 49 49	Fax: (1) 631 360 8222	Fax: (852) 24250 494	Fax: (44) 161 622 4446	
europe.sales@zetex.com	usa.sales@zetex.com	asia.sales@zetex.com	hq@zetex.com	

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